Fabrication and Characterization of Bilayer ZnO/Cu₄O₃ Thin Films for Optoelectronic Application

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Received: 17/06/2023; Accepted: 22/11/2023

Abstract

Herein, we report the fabrication and characterization of pure ZnO, pure Cu₄O₃ and bilayer ZnO/Cu₄O₃ thin films using cost-effective nebulizer spray pyrolysis (NSP) method deposited on glass slide substrate. The microstructural, and optical, properties of the prepared films are studied using X-ray diffraction and UV-visible spectroscopy. The X-Ray diffraction (XRD) patterns revealed that all synthesized thin layer exhibit polycrystalline nature with würtzite hexagonal structure for pure ZnO sample and tetragonal structure for pure Cu₄O₃ film. However, the bilayer film revealed a domination of the ZnO and Cu₄O₃ with (002) diffraction plane present the preferential orientation. The obtained results indicate that the crystallite size of the deposited films vary from 7.47 to 10.45 nm. From UV-vis analysis, it was found that all thin layers exhibit highly optical transmission, and bilayer films present the maximum transmission more than 80% in the visible region. The Eg values of the prepared films were ranged between 2.92 and 3.18 eV. In addition, the optical parameters such as, the refractive index and extinction coefficient of all films were determined.

Keywords: ZnO, Cu₄O₃, Thin films, nebulized spray pyrolysis (NSP), X-ray diffraction, Optical properties.

Tob Regul Sci. ™ 2023 ;9(2): 1385-1393 DOI: doi.org/10.18001/TRS.9.2.85

1. Introduction:

In the past decade, Transition metal oxides (TMOs) such as ZnO, NiO, SnO₂ played a significant role due to its vast potential applications such as: transparent electronics [1], electrochemical capacitors [2], gas sensor [3], heterojunction solar cells [4], catalysis [5] and electrodes in lithium batteries [6]. Zinc oxide (ZnO) is one of the important n-type semiconductor which is cost-effective, non-toxic, stable, abundance, high excitonic binding energy (60 meV), good mechanical and chemical stability and has a wide band gap of 3.2 eV [7,8]. Therefore, it is widely used in different fields such as; microelectronic devices, light-emitting diodes, laser devices and optoelectronic devices [9-12]. Whereas, copper oxides (CuO)

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received significant attention because of its low cost and abundant metal, non-toxic and favorable environment [13]. their oxides such as CuO, Cu₂O and Cu₄O₃ are natural p-type semiconductors with a direct band gap close ~1.4 eV suitable to PV applications as absorber layer [14]. For the fabrication of ZnO and Cu₄O₃ thin films, various methods were employed such as; electrochemical deposition, hydrothermal, thermal evaporation, sol-gel method, and nebulizer spray pyrolysis [15-19]. Among these methods nebulizer spray pyrolysis routes is a low-cost and easy to control the deposition parameters such as film deposition rate, concentration, thickness, etc [20]. The aim of this work focused on fabrication of pure ZnO pure, pure Cu₄O₃ and bilayer ZnO/Cu₄O₃ thin films using nebulizer spray pyrolysis (NSP) method deposited on glass slide substrate at temperature maintained at 400°C. The structural and optical properties of the prepared films were investigated.

2. Experimental details

2.1. Synthesis of thin films

pure ZnO, pure Cu₄O₃ and bilayer ZnO/Cu₄O₃ thin films were synthesized using nebulizer spray pyrolysis (NSP) technique. First the ZnO precursor solution was obtained by dissolving 30 ml of de-ionized water and the required mass of dehydrated zinc acetate (Zn (CH₃COO)₂, 2H₂O) to get concentration of 0.1 mol/L-1. For preparing pure Cu₄O₃ solution, dissolving 0.1 mol/L-1 of copper chloride dehydrate (CuCl₂.2H₂O) in de-ionized water to obtain a final transparent solution. These starting solutions were stirred for about 30 min with a magnetic stirrer at room temperature a few drops of acetic acid was added separately to obtain homogenous solution. Before deposition process, microscopic glass slide (R217102) were cleaned with acetone and distilled water respectively for 10min, and then blowing dry with a compressed air. After that, the solution was sprayed onto heated substrates at 400°C in the air atmosphere. The distance between nozzle and the substrate was kept constant at 20 cm. After deposition of the ZnO and Cu₄O₃ thin films, the same procedure was repeated to get bilayer ZnO/Cu₄O₃ films. Finally, all prepared thin films were allowed to cool slowly at room temperature.

2.2 Thin films characterization

The structural properties of prepared thin films were investigated using X-ray diffraction Bruker D8 Advance equipped with X'Pert High Score under Cu K α (λ =1.5406Å) radiation in the range of 20° and 60°. The optical transmission spectra were carried out by through Agilent technologies cray series UV-Vis spectrophotometer (cray 100 UV-Vis) in the wavelength between 300 and 900 nm.

3. Result and discussions

3.1 Structural properties

The structural properties of the deposited pure ZnO, pure Cu_4O_3 and bilayer ZnO/Cu_4O_3 thin films are analyzed by using the X-ray Diffraction technique (XRD). Fig.1 represents the XRD patterns of all prepared samples. As can be seen from pure ZnO sample, we can distinct three fundamental diffraction angle located at 31.74° , 34.42° and 47.53° which correspond to the diffraction planes (100), (002) and (102), respectively. All these diffraction peaks can be indexed

to the hexagonal würtzite structure (JCPDS card no. 36–1451) [21]. A strong diffraction peak is observed at (100) plane which demonstrates that there is a high degree of crystallinity for the pure ZnO film. On other hand, the pure Cu_4O_3 film reveals peaks detected at 2θ =28.21°, 30.69°, 35.78° and 61.45° which corresponds to the Cu_4O_3 plane orientation of (112), (200), and (211), respectively, however the diffraction angle appeared at 2θ =50.42° corresponding to diffractions plane of (112), of monoclinic structure of CuO [22]. All detected peaks are matched well with the tetragonal structure of Cu_4O_3 (Paramelaconite, JCPDS 49-1830) and monoclinic structure of CuO (Tenorite, JCPDS 45-0936) respectively [23]. From the XRD patterns the intensity of the plane (200) present the strongest peaks which can considered as the preferred orientation. In addition, we can see from XRD patterns that the characteristic peaks of ZnO and Cu_4O_3 structure are detected, with appearance of new diffractions plane (004) and (301) corresponding to the tetragonal structure of Cu_4O_3 . Also it is clearly seen that the preferential orientation from this sample display at (002) peak corresponding to ZnO lattice structure plane, which indicating a perpendicular alignment of the c-axis.

The estimated average crystallite size of pure ZnO, pure Cu₄O₃ and bilayer films can be calculated using the well-known Scherrer's formula [24]:

$$D = \frac{0.9\lambda}{\beta \cos \theta} \tag{1}$$

Where D is the crystallite size, β is the full width at half-maximum (FWHM) of the most intense diffraction peak, λ is the X-ray wavelength (1.54056 Å) and θ is the Bragg angle at (100), (200), and (002) peak plane corresponding to pure ZnO, pure Cu₄O₃ and bilayer sample respectively. The calculated crystallite size values were found to be 10.45, 7.47, and 9.25 nm corresponding to pure ZnO, pure Cu₄O₃ and bilayer sample respectively. It can be seen that the maximum values of crystallite size have been determined for pure ZnO film that indicates the better crystallinity,

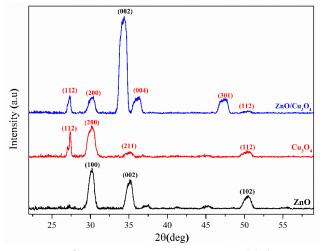


Fig. 1: X-ray diffraction patterns of pure ZnO, pure Cu₄O₃ and bilayer ZnO / Cu₄O₃ thin films.

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3.4 Optical properties

Optical transmittance spectra of the ZnO, Cu₄O₃ and ZnO/ Cu₄O₃ bilayer thin films are shown in Fig. 2. The analysis of these figures revealed that the transmittance of the bilayer samples has been display high average transmittance of (~80%) in the range of 300–900 nm compared to pure ZnO and Cu₄O₃ films, this behavior indicating high quality, and low dispersion of light [25]. Whereas the lower transmittance around (~74%) presented in the pure ZnO films. An abrupt diminution can be observing in the transmittance spectra from all samples has been found in the range around 350–380 nm region that indicates the inter-band absorption edges [26].

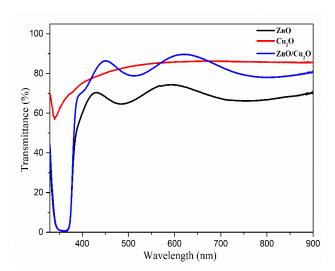


Fig.2: Transmittance spectra of pure ZnO, pure Cu₄O₃ and bilayer ZnO / Cu₄O₃ thin films.

In order to evaluate the band gap energy (Eg) of all deposited films, the Tauc formula can be used which imply the relationship between the absorption coefficient (α) and the incident photon energy ($h\nu$) as follows [27]:

$$\alpha = \frac{B}{h\nu} (h\nu - E_g)^{\frac{1}{2}} \tag{2}$$

Where B is constant related with the nature of transition, α is the absorption coefficient, $h\nu$ is the photon energy and Eg is the band gap energy.

the absorption coefficient α can be estimated from the transmittance T, and the films thickness d using the following equation [27]:

$$\alpha = \frac{1}{d} \ln \left(\frac{1}{T} \right) \tag{3}$$

The optical band gap values of pure ZnO, Cu_4O_3 and bilayer ZnO/ Cu_4O_3 films have been evaluated by extrapolating the linear portion of the plot of $(\alpha h\nu)2$ versus $(h\nu)$ as illustrated in Fig.3. The obtained results show that the Eg values for pure ZnO (2.92 eV) and for pure Cu_4O_3

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(3.18 eV). However, from bilayer ZnO/Cu₄O₃ films are (3.17 eV), which authorizes its use as an optical window in solar cells.

The optical band gap values of pure ZnO, Cu_4O_3 and bilayer ZnO/ Cu_4O_3 films have been evaluated by extrapolating the linear portion of the plot of $(\alpha h \nu)2$ versus $(h \nu)$ as illustrated in Fig.3. The obtained results show that the Eg values for pure ZnO (2.92 eV) and for pure Cu_4O_3 (3.18 eV). However, from bilayer ZnO/ Cu_4O_3 films are (3.17 eV), which authorizes its use as an optical window in solar cells.

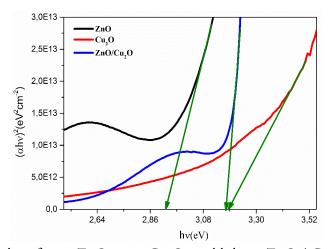


Fig.3: Tauc's plot of pure ZnO, pure Cu₄O₃ and bilayer ZnO / Cu₄O₃ thin films.

The refractive index (n) plays significant factors in optical devices, optoelectronic applications optical communication, and optical amplifiers etc. The refractive index (n) of all prepared thin films are calculated using the following equations [27]:

$$n = \frac{(1+R)}{(1-R)} \pm \sqrt{\frac{4R}{(1-R)^2} - k^2}$$
 and $k = \frac{\alpha\lambda}{4\pi}$ (4)

Where, k, R, λ and α are Extinction coefficient, the reflectance, wavelength and absorption coefficient respectively. The variation of n and k values as a function of wavelength is shown in Fig. 4 and Fig. 5 respectively.

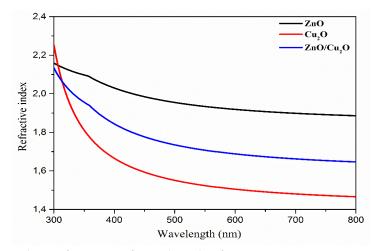


Fig.4: Refractive index as function of wavelength of pure ZnO, pure Cu_4O_3 and bilayer ZnO $/Cu_4O_3$ thin films.

It is can be seen that the refractive index (n) of all samples is decreased slightly with increase in wavelength, this behavior can be due to the reduction and the loss of light after passing through the required material [28]. In all thin layers, the extinction coefficient spectra were also decreased with increasing the wavelength of photon. Furthermore, the k values are very small and approximately behind to zero, this result support that the prepared films are transparent in visible region and with smooth surface [29].

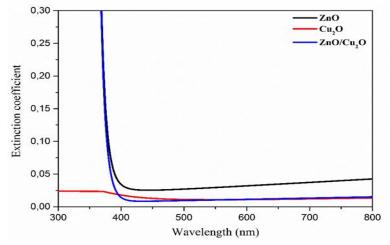


Fig.5: Extinction coefficient as function of wavelength of pure ZnO, pure Cu_4O_3 and bilayer ZnO/Cu_4O_3 thin films.

4. Conclusion

In this work, pure ZnO, pure Cu_4O_3 and bilayer ZnO $/Cu_4O_3$ thin films have been achieved using cost effective nebulizer spray pyrolysis (NSP) technique at 400° C on glass slide substrates. Investigation of the prepared films has been done using X-ray diffraction and UV-visible spectrophotometer. X-ray diffraction patterns from pure ZnO sample indicate a polycrystalline nature with würtzite hexagonal crystal structure, and the preferred orientation was along (100) plane. Whereas, pure Cu_4O_3 film have tetragonal structure with (200) diffraction plane as

preferential orientations. In addition, the XRD analysis of bilayer sample showed a domination of the ZnO and Cu_4O_3 with (002) diffraction plane present the preferential orientation. The crystallite size of all samples was found to vary from 7.47 to 10.45 nm. The bilayer ZnO/Cu_4O_3 thin film showed high average optical transmission around 80% in the visible region. Hence, the estimated optical band gap was found to be in the range 2.92-3.18 eV in all films. The other optical constants namely refractive index and extinction coefficient are found to decreases as function of wavelength. As a result, it can be assumed that the bilayer ZnO/Cu_4O_3 thin film can be considered as good candidate for optoelectronics devises.

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